PROCESS CPD76X

Schottky Diode

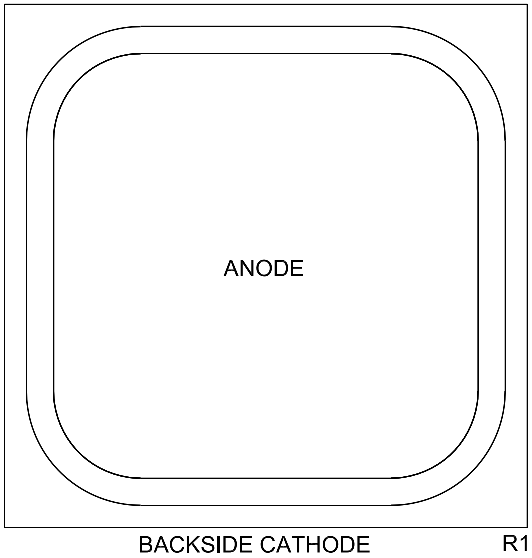
1 Amp Schottky Diode Chip

Central Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	32 x 32 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	27 x 27 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



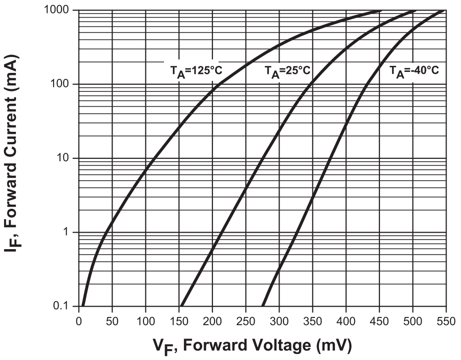
GROSS DIE PER 5 INCH WAFER
16,276

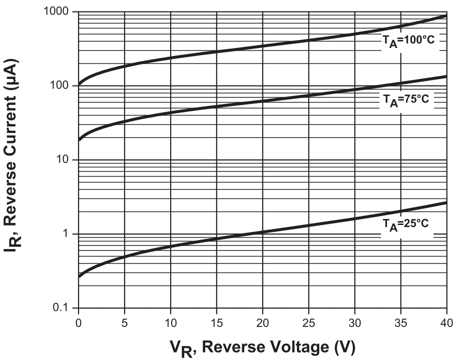
PRINCIPAL DEVICE TYPES
CMLSH1-40
CXSH-4
CTLSH1-40M832D

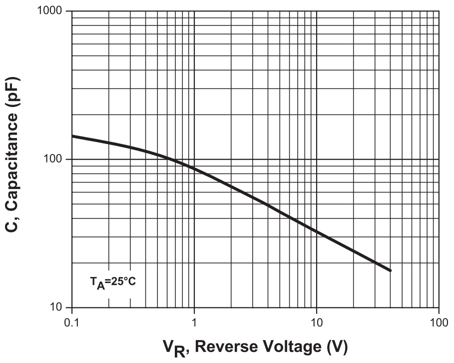
R2 (22-March 2010)

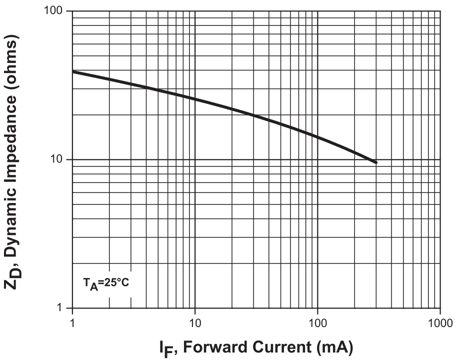
PROCESS CPD76X

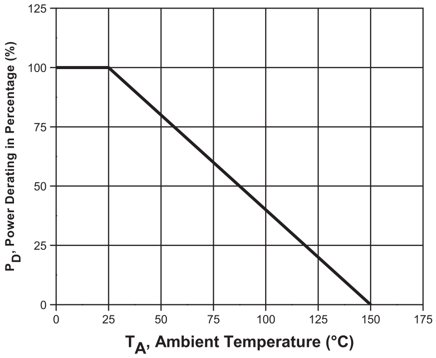
Typical Electrical Characteristics


Forward Voltage


Leakage Current


Capacitance


Forward Dynamic Impedance


Normalized Power Derating